## Miguel Zabala

List of Publications by Year in descending order

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516710 580821 52 694 16 25 h-index citations g-index papers 52 52 52 961 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	Synaptic devices based on HfO2 memristors. , 2021, , 383-426.		2
2	Study of RTN signals in resistive switching devices based on neural networks. Solid-State Electronics, 2021, 183, 108034.	1.4	5
3	Analysis of the Characteristic Current Fluctuations in the High Resistance State of HfO2-based Memristors. , 2021, , .		0
4	Capacitance Electrochemical pH Sensor Based on Different Hafnium Dioxide (HfO2) Thicknesses. Chemosensors, 2021, 9, 13.	3.6	19
5	Methodology for the characterization and observation of filamentary spots in HfOx-based memristor devices. Microelectronic Engineering, 2020, 223, 111232.	2.4	17
6	Electrochemical Capacitive K <sup>+</sup> EMIS Chemical Sensor Based on the Dibromoaza[7]helicene as an Ionophore for Potassium Ions Detection. Electroanalysis, 2016, 28, 2892-2899.	2.9	23
7	Development of a novel capacitance electrochemical biosensor based on silicon nitride for ochratoxin A detection. Sensors and Actuators B: Chemical, 2016, 234, 446-452.	7.8	38
8	Optimization of low-resistance strip sensors process and studies of radiation resistance. , 2015, , .		0
9	Investigation of the resistive switching behavior in Ni/HfO <inf>2</inf> -based RRAM devices., 2015, , .		2
10	Effect of the blistering of ALD Al <inf>2</inf> O <inf>3</inf> films on the silicon surface in Al-Al <inf>2</inf> O <inf>3</inf> -Si structures., 2015,,.		2
11	Development of a capacitive chemical sensor based on Co(II)-phthalocyanine acrylate-polymer/HfO <sub>2</sub> /SiO <sub>2</sub> for detection of perchlorate. Journal of Sensors and Sensor Systems, 2015, 4, 17-23.	gt#S#	12
12	A Fully Integrated Electrochemical BioMEMS Fabrication Process for Cytokine Detection: Application for Heart Failure. Procedia Engineering, 2014, 87, 377-379.	1.2	8
13	Analysis of the Switching Variability in <inline-formula> <tex-math notation="TeX">\$hbox{Ni/HfO}_{2}\$</tex-math></inline-formula> -Based RRAM Devices. IEEE Transactions on Device and Materials Reliability, 2014, 14, 769-771.	2.0	71
14	Low-resistance strip sensors for beam-loss event protection. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2014, 765, 252-257.	1.6	2
15	Functional and performance evaluation of low-resistance strip sensors for beam-loss event protection. , 2014, , .		1
16	A Novel Three-Dimensional Biosensor Based on Aluminum Oxide: Application for Early-Stage Detection of Human Interleukin-10. Methods in Molecular Biology, 2014, 1172, 49-64.	0.9	10
17	Impact of electrical stress on the electrical characteristics of 2MeV electron irradiated metal-oxide-silicon capacitors with atomic layer deposited Al2O3, HfO2 and nanolaminated dielectrics. Solid-State Electronics, 2013, 89, 198-206.	1.4	5
18	Charge trapping analysis of Al2O3 films deposited by atomic layer deposition using H2O or O3 as oxidant. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, .	1.2	18

#	Article	IF	CITATIONS
19	Thin dielectric films grown by atomic layer deposition: Properties and applications. , 2013, , .		O
20	Defect assessment and leakage control in atomic layer deposited Al <inf>2</inf> O <inf>3</inf> and HfO <inf>2</inf> dielectrics., 2013,,.		0
21	2MeV electron irradiation effects on the electrical characteristics of MOS capacitors with ALD Al2O3 dielectrics of different thickness. Microelectronics Reliability, 2013, 53, 1333-1337.	1.7	6
22	2 MeV electron irradiation effects on bulk and interface of atomic layer deposited high-k gate dielectrics on silicon. Thin Solid Films, 2013, 534, 482-487.	1.8	8
23	Charge trapping and electrical degradation in atomic layer deposited Al2O3 films. Microelectronic Engineering, 2013, 109, 57-59.	2.4	10
24	Diazonium modified gold microelectrodes onto polyimide substrates for impedimetric cytokine detection with an integrated Ag/AgCl reference electrode. Sensors and Actuators B: Chemical, 2013, 189, 165-172.	7.8	33
25	2 MeV electron irradiation effects on the electrical characteristics of metal–oxide–silicon capacitors with atomic layer deposited Al2O3, HfO2 and nanolaminated dielectrics. Solid-State Electronics, 2013, 79, 65-74.	1.4	23
26	Diode Characteristics and Thermal Donor Formation in Germanium-Doped Silicon Substrates. ECS Transactions, 2013, 50, 177-186.	0.5	1
27	Blistering of atomic layer deposition Al2O3 layers grown on silicon and its effect on metal–insulator–semiconductor structures. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	23
28	Electrical characterization of atomic-layer-deposited hafnium oxide films from hafnium tetrakis(dimethylamide) and water/ozone: Effects of growth temperature, oxygen source, and postdeposition annealing. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	25
29	Bow Free 4" Diameter 3C-SiC Epilayers Formed upon Wafer-Bonded Si/SiC Substrates. ECS Solid State Letters, 2012, 1, P85-P88.	1.4	5
30	A novel biosensor based on hafnium oxide: Application for early stage detection of human interleukin-10. Sensors and Actuators B: Chemical, 2012, 175, 201-207.	7.8	85
31	Comparative Analysis of MIS Capacitance Structures With High-k Dielectrics Under Gamma, \$^{16}\$O and p Radiation. IEEE Transactions on Nuclear Science, 2012, 59, 767-772.	2.0	1
32	Cytokine Detection using Diazonium Modified Gold Microelectrodes Onto Polyimide Substrates with Integrated Ag/AgCl Reference Electrode. Procedia Engineering, 2012, 47, 1181-1184.	1,2	6
33	Comparative analysis of MIS capacitive structures with high-K dielectrics under gamma, <sup>16</sup> O and p radiation., 2011,,.		0
34	Negative-resistance effect in Al <inf>2</inf> O <inf>3</inf> based and nanolaminated MIS structures. , 2011, , .		0
35	Deposition Temperature and Thermal Annealing Effects on the Electrical Characteristics of Atomic Layer Deposited Al2O3 Films on Silicon. Journal of the Electrochemical Society, 2011, 158, G108.	2.9	54
36	Novel Capacitance Biosensor Based on Hafnium Oxide for Interleukin-10 Protein Detection. Procedia Engineering, 2011, 25, 972-975.	1,2	3

#	Article	IF	Citations
37	Comparison between Al <inf>2</inf> O <inf>3</inf> thin films grown by ALD using H <inf>2</inf> O or O <inf>3</inf> as oxidant source., 2011,,.		6
38	Soft breakdown in irradiated high-lº nanolaminates. Microelectronic Engineering, 2011, 88, 1425-1427.	2.4	5
39	Electrical characteristics of metal-insulator-semiconductor structures with atomic layer deposited Al2O3, HfO2, and nanolaminates on different silicon substrates. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01AA07.	1.2	41
40	Electrical characterization of high-k based metal-insulator-semiconductor structures with negative resistance effect when using Al2O3 and nanolaminated films deposited on p-Si. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 01A901.	1.2	14
41	Electron Irradiation Effects on Atomic Layer Deposited High-k Gate Dielectrics. ECS Transactions, 2011, 41, 349-359.	0.5	0
42	Fabrication of PPF Electrodes by a Rapid Thermal Process. Journal of the Electrochemical Society, 2011, 158, H63.	2.9	21
43	Deposited Thin SiO[sub 2] for Gate Oxide on n-Type and p-Type GaN. Journal of the Electrochemical Society, 2010, 157, H1008.	2.9	20
44	Integration of HfO2 on Si/SiC heterojunctions for the gate architecture of SiC power devices. Applied Physics Letters, 2010, 97, 013506.	3.3	8
45	Effect of Processing Conditions on the Electrical Characteristics of Atomic Layer Deposited Al <sub>2</sub> O <sub>3</sub> and HfO <sub>2</sub> Films. ECS Transactions, 2010, 28, 213-221.	0.5	10
46	Impact of silicon substrate germanium doping on diode characteristics and on thermal donor formation. Physica B: Condensed Matter, 2009, 404, 4723-4726.	2.7	4
47	Thin high-k dielectric layers deposited by ALD. , 2009, , .		3
48	Evaluation of Surface Passivation Layers for Bulk Lifetime Estimation of High Resistivity Silicon for Radiation Detectors. Solid State Phenomena, 2008, 131-133, 431-436.	0.3	1
49	Evaluation of surface passivation layers for bulk lifetime estimation of high resistivity silicon for radiation detectors. , 2007, , .		1
50	Hydrogen-selective microelectrodes based on silicon needles. Sensors and Actuators B: Chemical, 2003, 91, 76-82.	7.8	39
51	CMOS integrated pressure sensor optimization using electrical network simulator-FEM tool coupling. Journal of Micromechanics and Microengineering, 1999, 9, 109-112.	2.6	3
52	Characterisation of HfO <sub>2</sub> /Si/SiC MOS Capacitors. Materials Science Forum, 0, 679-680, 674-677.	0.3	0